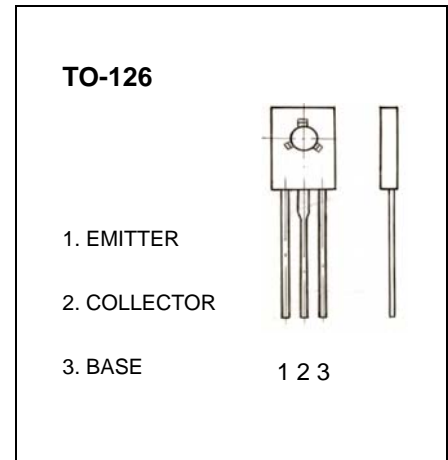


D882 TRANSISTOR (NPN)



MAXIMUM RATINGS* $T_A=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CB0}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	3	A
P_D	Total Device Dissipation	1.25	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Junction and Storage Temperature	-55-150	$^{\circ}\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

ELECTRICAL CHARACTERISTICS($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CB0}$	$I_C=100\mu\text{A}$, $I_E=0$	40			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	$I_C=10\text{ mA}$, $I_B=0$	30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E=100\text{ mA}$, $I_C=0$	6			V
Collector cut-off current	I_{CB0}	$V_{CB}=40\text{ V}$, $I_E=0$			1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=30\text{ V}$, $I_B=0$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{ V}$, $I_C=0$			1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=2\text{ V}$, $I_C=1\text{ A}$	60		400	
	$h_{FE(2)}$	$V_{CE}=2\text{ V}$, $I_C=100\text{ mA}$	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{ A}$, $I_B=0.2\text{ A}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=2\text{ A}$, $I_B=0.2\text{ A}$			1.5	V
Transition frequency	f_T	$V_{CE}=5\text{ V}$, $I_C=0.1\text{ mA}$ $f=10\text{ MHz}$	50			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

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Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

Typical Characteristics

